TOSHIBA Photocoupler IRED & Photo-IC

TLP2601

Isolated Line Receiver Simplex / Multiplex Data Transmission Computer-Peripheral Interface Microprocessor System Interface Digital Isolation for A/D, D/A Conversion Direct Replacement for HCPL-2601

The TOSHIBA TLP2601 a photocoupler which combines an IRED as the emitter and an integrated high gain, high speed photodetector. The output of the detector circuit is an open collector, Schottky clamped transistor.

A Faraday shield integrated on the photodetector chip reduces the effects of capacitive coupling between the input LED emitter and the high gain stages of the detector. This provides an effective common mode transient immunity of $1000V/\mu s$.

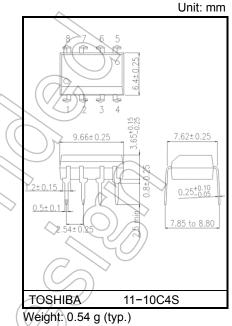
- Input current thresholds: IF = 5mA (max)
- Isolation voltage: 2500Vrms (min)
- Switching speed: 10MBd

TOSHIBA

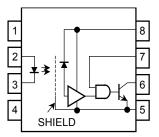
- Common mode transient immunity: 1000V/µs (min)
- Guaranteed performance over temp.: 0°C to 70°C
- UL-recognized: UL 1577, File No.E67349
- cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

Truth Table (positive logic)

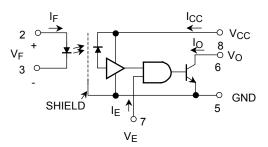
Input	Enable	Output
Н	н	L
L	Н	н
Н		Н
L		н 🔿
		2



Pin Configuration (top view)



Schematic



A 0.01 to $0.1 \mu F$ bypass capacitor must be connected between pins 8 and 5 (see Note 1)

Start of commercial production 1985-01

Recommended Operating Conditions

Characteristic	Symbol	Min	Тур.	Max	Unit	
Input current, low level	I _{FL}	0	_	250	μA	
Input current, high level	IFH	6.3 (*)		20	mA	
Supply voltage**, output	V _{CC}	4.5		5.5	v <	
High level enable voltage	VEH	2.0		Vcc	V	$\langle \rangle$
Low level enable voltage	VEL	0		0.8	V	\bigcirc
Fan out (TTL load)	Ν	_	-	8	(7)	\sim
Operating temperature	Topr	0		70	o, C	リ

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

(*) 6.3mA is a guard banded value which allows for at least 20% CTR degradation.

Initial input current threshold value is 5.0 mA or less.

**This item denotes operating ranges, not meaning of recommended operating conditions

Absolute Maximum Ratings (no derating required)

	- · ·				
	Characteristic	Symbol	Rating	Unit	
	Forward current		20	mA	
LED	Reverse voltage	VR	5	$\langle v \rangle$	
	Diode power dissipation	PD	100	mW	
	Diode power dissipation derating (Ta ≥70°C)	∆P _D /°C	-1.8	mW/°C	
	Junction Temperature	Тј	125	°C	
	Output current	lo	25	mA	
	Output voltage	Vo	-0.5 to 7	V	
ector	Supply voltage (1 minute maximum)	Vcc	7	V	
	Enable input voltage (not to exceed V _{CC} by more than 500mV)	VE	5.5	V	
	Output power dissipation	PC	40	mW	
	Output Power dissipation derating (Ta ≥ 70°C)	ΔPc/°C	-0.7	mW / °C	
	Junction Temperature	Tj	125	°C	
Operating temperature range Storage Temperature range Lead Solder Temperature (10 s)		Topr	-40 to 85	°C	
		T _{stg}	-55 to 125	°C	
		T _{sol}	260	°C	
Isola	tion voltage		2500	Vrms	
	.≤ 60 %, AC 60 s) (Note 10)	BVs	3540	Vdc	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(**) 1.6 mm below seating plane.

Electrical Characteristics (Ta = 0°C to 70°C unless otherwise noted)

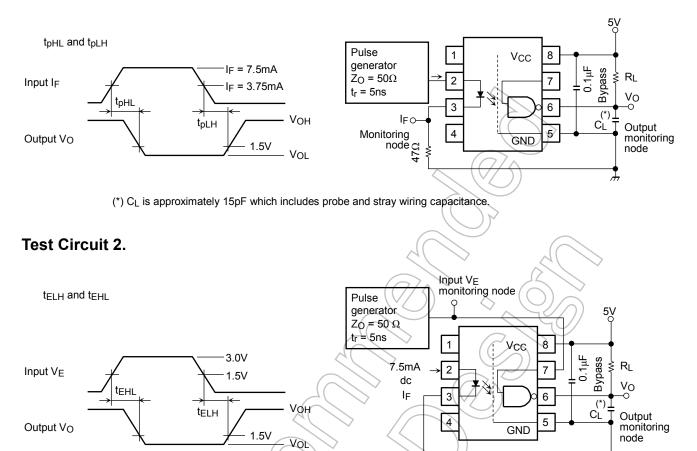
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
High level output current	ЮН	V _{CC} = 5.5 V, V _O = 5.5 V I _F = 250 μA, V _E = 2.0 V	_	1	250	μA
Low level output voltage	V _{OL}	V _{CC} = 5.5 V, I _F = 5 mA V _E = 2.0 V, I _{OL} (sinking) = 13 mA	-	0.4	0.6	V
High level supply current	Іссн	V_{CC} = 5.5 V, I _F = 0 A, V _E = 0.5 V	- (T	15	mA
Low level supply current	ICCL	V_{CC} = 5.5 V, I _F = 10 mA, V _E = 0.5 V		12	19	mA
Low level enable current	IEL	V _{CC} = 5.5 V, V _E = 0.5 V	<u> </u>	-1.6	-2.0	mA
High level enable current	IEH	V _{CC} = 5.5 V, V _E = 2.0 V		-1	_	mA
High level enable voltage	VEH	(Note 11)	2.0	-	_	v
Low level enable voltage	V _{EL}	- 20	$>$ _	(0.8	v
Input forward voltage	VF	I _F = 10 mA, Ta = 25 °C	_	1.65	1.75	V
Input reverse breakdown voltage	BVR	I _R = 10 μA, Ta = 25 °C	5 <	R) –	V
Input capacitance	CIN	VF = 0 V, f = 1 MHz	-0	45	_	pF
Input diode temperature coefficient	$\Delta V_F / \Delta T_A$	IF = 10 mA	(7)	-2.0	_	mV / °C
Input-output insulation leakage current	II-O	Relative humidity = 45 % Ta=25 °C, t = 5 s V⊨o = 3000 Vdc, (Note 10)		_	1	μΑ
Resistance (input-output)	RI-O	V _{HO} = 500 V, R.H.≤ 60 % (Note 10)	5×10 ¹⁰	10 ¹⁴	_	Ω
Capacitance (input-output)	CI-O	f = 1 MHz (Note 10)	_	0.6	_	pF

(**) All typ.values are at $V_{CC} = 5 V$, Ta = 25 °C.

Switching Characteristics (Ta = 25°C, Vcc = 5 V)

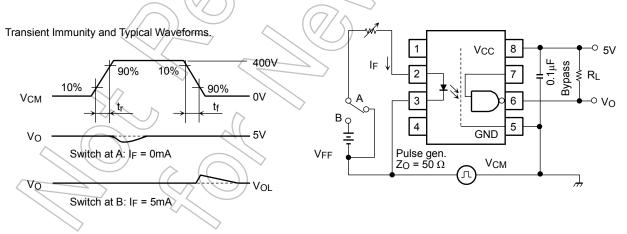
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time to high output level	t _{pLH}		R _L = 350 Ω, C _L = 15 pF	_	60	75	ns
Propagation delay time to low output level	t _{pHL}	1	IF = 7.5 mA (Note 2), (Note 3),		60	75	ns
Output rise time (10-90%)	tr		(Note 4)&(Note 5)	(-)	30	_	ns
Output fall time (90–10%)	tf	-)	30	_	ns
Propagation delay time of enable from V _{EH} to V _{EL}	telh	_	RL = 350 Ω, CL ⇒ 15 pF IF = 7.5 mA	<u>)</u>	25	_	ns
Propagation delay time of enable from VEL to VEH	tehl	2	VEH = 3.0 V VEL = 0.5 V (Note 6) & (Note 7)	_	25	_	ns
Common mode transient immunity at high output level	СМн	3	$V_{CM} = 400 V$ RL = 350 Ω VO(min) = 2 V IF = 0 mA, (Note 9)	1000	10000		V/µs
Common mode transient immunity at low output level	CML	3	$V_{CM} = 400 V$ RL = 350 Ω VO(max) = 0.8 V IF = 7.5 mA, (Note 8)	-1000	-10000	_	V/µs

Test Circuit 1.

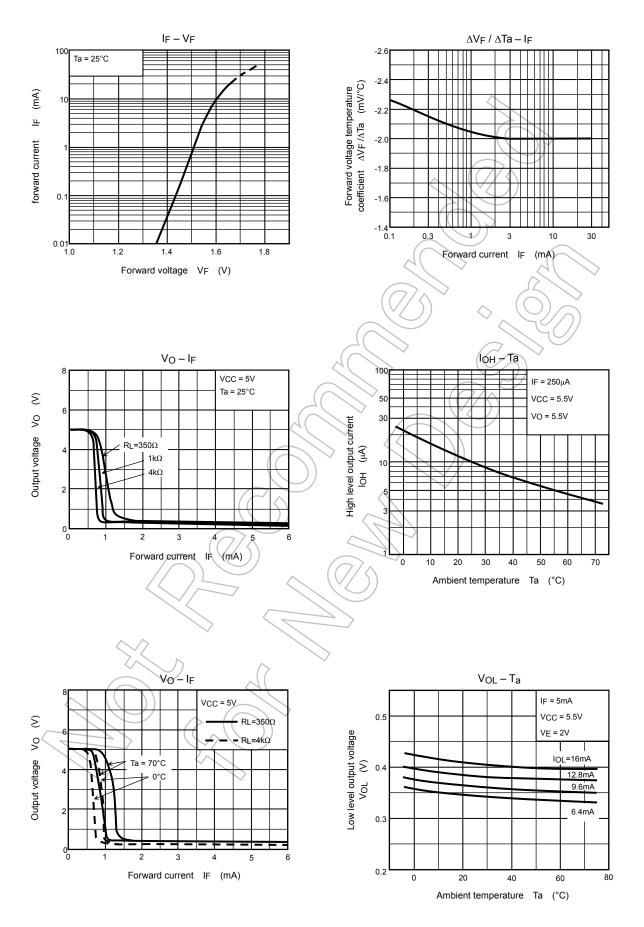


(*) C_L is approximately 15pF which includes probe and stray wiring capacitance.

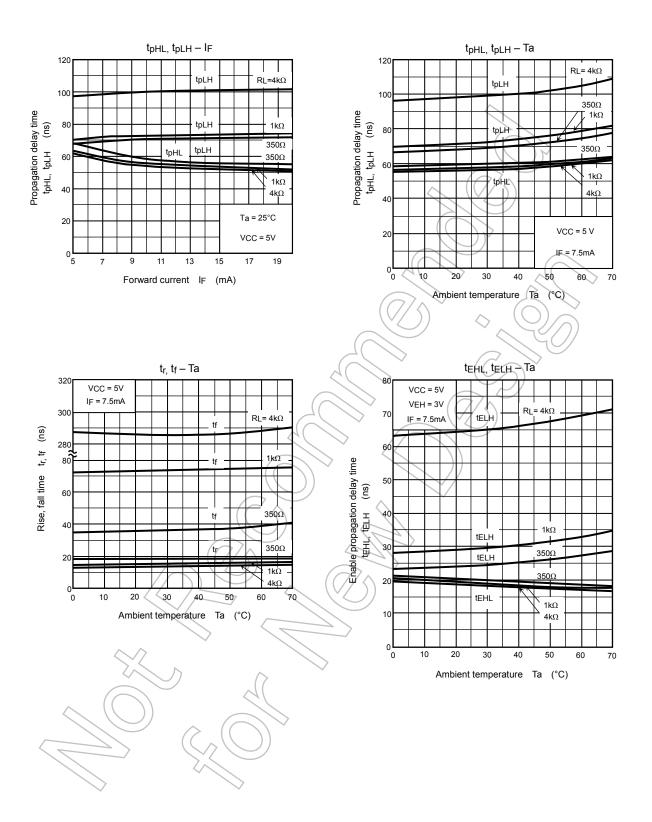
Test Circuit 3.



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NOTE: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



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Notes

- 1. The V_{CC} supply voltage to each TLP2601 isolator must be bypassed by a 0.1 μ F capacitor of larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to the package V_{CC} and GND pins of each device.
- 2. t_{pHL} · Propagation delay is measured from the 3.75 mA level on the low to high transition of the input current pulse to the 1.5 V level on the high to low transition of the output voltage pulse.
- 3. t_{pLH} Propagation delay is measured from the 3.75 mA level on the high to low transition of the input current pulse to the 1.5 V level on the low to high transition of the output voltage pulse.
- 4. tf Fall time is measured from the 10 % to 90 % levels of the high to low transition on the output pulse.
- 5. tr · Rise time is measured from the 90 % to 10 % levels of the low to high transition on the output pulse.
- 6. tEHL Enable input propagation delay is measured from the 1.5 V level on the low to high transition of the input voltage pulse to the 1.5 V level on the high to low transition of the output voltage pulse.
- 7. tELH Enable input propagation delay is measured from the 1.5 V level on the high to low transition of the input voltage pulse to the 1.5 V level on the low to high transition of the output voltage pulse.
- 8. CML The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state (i.e. VOUT < (0.8 V). Measured in volts per microsecond (V / μs).
- 9. CM_H
 The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the high state (i.e. VOUT > 2.0 V). Measured in volts per microsecond (V / μs). Volts/microsecond can be translated to sinusoidal voltages:

$$V / \mu s = \frac{(dv_{CM})}{dt} = f_{CM} V_{CM} (p.p.)$$

Example: $V_{CM} = 318 V_{pp}$ when f_{CM} = 1 MHz using CML and CM_H = 1000 V / μ s data sheet specified minimum.

- 10. Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together, and Pins 5, 6, 7 and 8 shorted together.
- 11. Enable No pull up resistor required as the device has an internal pull up resistor.

input

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